

# **Excellent Integrated System Limited**

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STMicroelectronics FERD30SM100DJFTR

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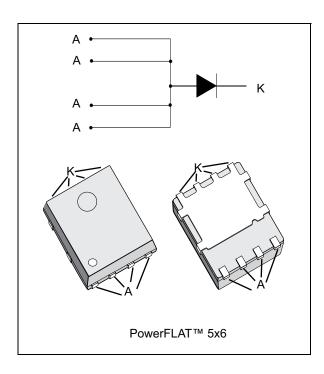




# FERD30SM100DJF

#### Field effect rectifier

Datasheet - production data



### **Description**

The FERD30SM100DJF is based on a proprietary technology that achieves the best in class  $V_F/I_R$  trade-off for a given silicon surface.

This 100 V rectifier has been optimized for use in confined applications where both efficiency and thermal performance are key.

Table 1. Device summary

Symbol	Value
I <sub>F(AV)</sub>	30 A
$V_{RRM}$	100 V
T <sub>j (max)</sub>	+175 °C
V <sub>F</sub> (typ)	0.395 V

#### **Features**

- · ST proprietary process
- Reduce leakage current
- Low forward voltage drop
- High frequency operation
- ECOPACK®2 compliant component

TM: PowerFLAT is a trademark of STMicroelectronics

 January 2015
 DocID027306 Rev 1
 1/8



Characteristics FERD30SM100DJF

### 1 Characteristics

Table 2. Absolute ratings (limiting values, at 25 °C, unless otherwise specified, anode terminals short-circuited)

Symbol	Parameter			Unit
$V_{RRM}$	Repetitive peak reverse voltage			V
I <sub>F(RMS)</sub>	Forward rms current			Α
I <sub>F(AV)</sub>	Average forward current, $\delta = 0.5$	T <sub>c</sub> = 100 °C	30	Α
I <sub>FSM</sub>	Surge non repetitive forward current $t_p = 10 \text{ ms sinusoidal}$		180	Α
T <sub>stg</sub>	Storage temperature range			°C
T <sub>j</sub> <sup>(1)</sup>	Maximum operating junction temperature			°C

<sup>1.</sup>  $\frac{dPtot}{dT_j} < \frac{1}{Rth(j-a)}$  condition to avoid thermal runaway for a diode on its own heatsink

Table 3. Thermal resistance

Symbol	Parameter	Value (max)	Unit
R <sub>th(j-c)</sub>	Junction to case	2.6	°C/W

Table 4. Static electrical characteristics (anode terminals short-circuited)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
	Reverse leakage current	T <sub>j</sub> = 25 °C	$V_R = V_{RRM}$	-	-	150	μΑ
I <sub>R</sub> <sup>(1)</sup>		T <sub>j</sub> = 125 °C		-	8	16	mA
		T <sub>j</sub> = 125 °C	V <sub>R</sub> = 70 V	-	-	9	
V <sub>F</sub> <sup>(2)</sup>	Forward voltage drop	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 5 A	-	-	0.48	V
		T <sub>j</sub> = 125 °C		-	0.395	0.435	
		T <sub>j</sub> = 25 °C	I <sub>F</sub> = 10A	-	-	0.595	
		T <sub>j</sub> = 125 °C		-	0.51	0.555	
		T <sub>j</sub> = 25 °C	I <sub>F</sub> = 30 A	-		0.97	
		T <sub>j</sub> = 125 °C		-	0.665	0.735	

<sup>1.</sup> Pulse test:  $t_p = 5$  ms,  $\delta < 2\%$ 

To evaluate the conduction losses use the following equation:

$$P = 0.562 \times I_{F(AV)} + 0.0057 I_{F(RMS)}^{2}$$



<sup>2.</sup> Pulse test:  $t_p$  = 380  $\mu$ s,  $\delta$  < 2%



FERD30SM100DJF Characteristics

Figure 1. Average forward power dissipation versus average forward current

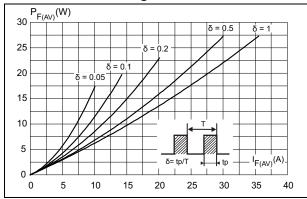


Figure 2. Average forward current versus ambient temperature ( $\delta = 0.5$ )

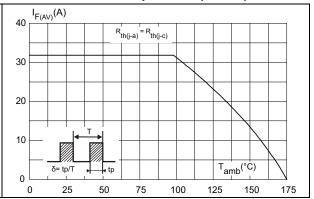
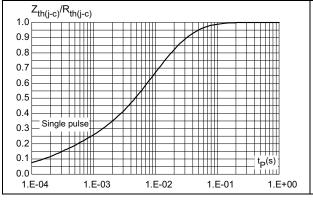


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Reverse leakage current versus reverse voltage applied (typical values)



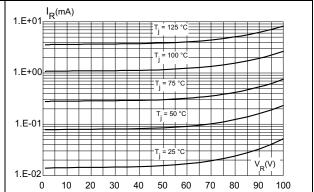
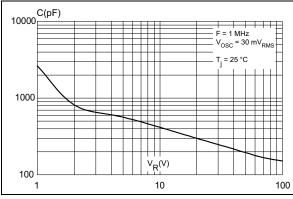
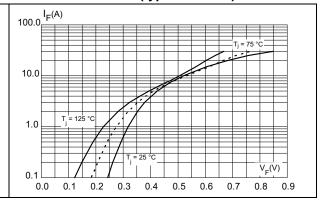


Figure 5. Junction capacitance versus reverse voltage applied (typical values)

Figure 6. Forward voltage drop versus forward current (typical values)

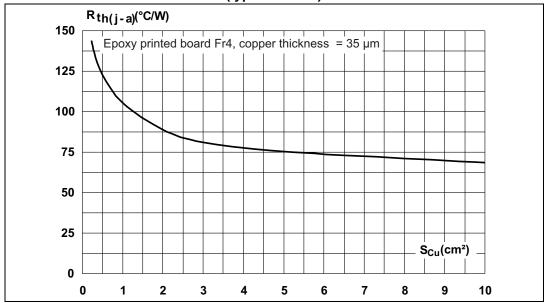






Characteristics FERD30SM100DJF

Figure 7. Thermal resistance junction to ambient versus copper surface under tab (typical values)







FERD30SM100DJF Package information

## 2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="https://www.st.com">www.st.com</a>. ECOPACK<sup>®</sup> is an ST trademark.

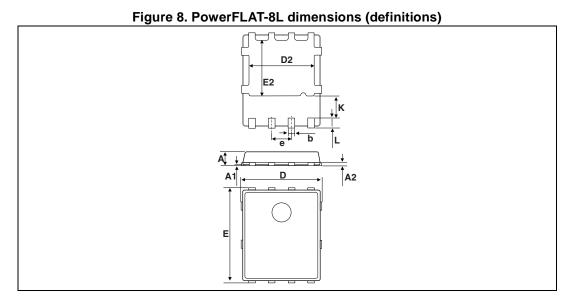


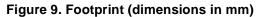
Table 5. PowerFLAT-8L dimensions (values)

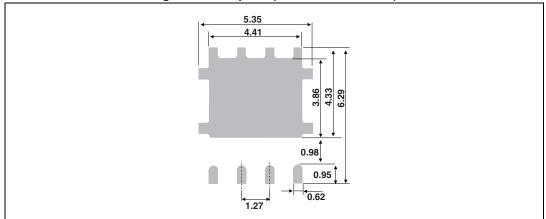
		Dimensions				
Ref.	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
А	0.80		1.00	0.031		0.039
A1	0.02		0.05	0.001		0.002
A2		0.25			0.010	
b	0.30		0.50	0.012		0.020
D		5.20			0.205	
D2	4.11		4.31	0.162		0.170
е		1.27			0.050	
Е		6.15			0.242	
E2	3.50		3.70	0.138		0.146
L	0.50		0.80	0.020		0.031
K	1.275		1.575	0.050		0.062





Package information FERD30SM100DJF









FERD30SM100DJF

**Ordering information** 

# 3 Ordering information

**Table 6. Ordering information** 

Order code	Marking	Package	Weight	Base qty	Delivery mode
FERD30SM100DJF	F30SM 100	PowerFLAT 5x6	95 mg	3000	Tape and reel

## 4 Revision history

Table 7. Document revision history

Date	Revision	Changes
09-Jan-2015	1	Initial release.





# Distributor of STMicroelectronics: Excellent Integrated System Limited Datasheet of FERD30SM100DJFTR - DIODE GP 100V 30A POWERFLAT

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FERD30SM100DJF

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